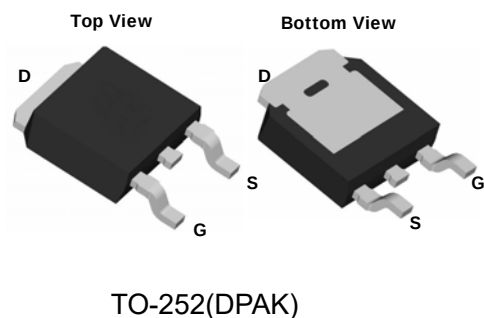


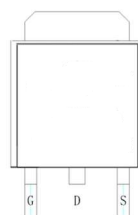
Features

- -30V, -80A
 $R_{DS(ON)} \text{ Typ} = 4.3\text{m}\Omega @ V_{GS} = -10\text{V}$
 $R_{DS(ON)} \text{ Typ} = 6.8\text{m}\Omega @ V_{GS} = -4.5\text{V}$
- Advanced Trench Technology
- Excellent $R_{DS(ON)}$ and Low Gate Charge
- 100% UIS TESTED!
- 100% ΔV_{ds} TESTED!

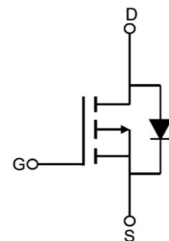


Application

- Load Switch
- PWM Application
- Power Management



Pin Assignment



Schematic Diagram

Absolute Maximum Ratings (@ $T_J = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Value	Units	
V _{DS}	Drain-to-Source Voltage	-30	V	
V _{GS}	Gate-to-Source Voltage	±20	V	
I _D	Continuous Drain Current	T _C = 25°C	-80	A
		T _C = 100°C	-48	A
I _{DM}	Pulsed Drain Current ⁽¹⁾	-320	A	
E _{AS}	Single Pulsed Avalanche Energy ⁽²⁾	441	mJ	
P _D	Power Dissipation	T _C = 25°C	62.5	W
R _{θJC}	Thermal Resistance, Junction to Case	2	°C/W	
T _J , T _{STG}	Junction & Storage Temperature Range	-55 to 150	°C	

**Electrical Characteristics** ($T_J = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
Off Characteristics						
V _{(BR)DSS}	Drain-Source Breakdown Voltage	I _D = -250μA, V _{GS} = 0V	-30	-	-	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = -30V, V _{GS} = 0V	-	-	-1.0	μA
I _{GSS}	Gate-Body Leakage Current	V _{DS} = 0V, V _{GS} = ±20V	-	-	±100	nA
On Characteristics						
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} , I _D = -250μA	-1.1	-1.5	-2.2	V
R _{DS(ON)}	Static Drain-Source ON-Resistance ⁽³⁾	V _{GS} = -10V, I _D = -20A	-	4.3	6.5	mΩ
		V _{GS} = -4.5V, I _D = -10A	-	6.8	9.9	mΩ
Dynamic Characteristics						
C _{iss}	Input Capacitance	V _{GS} = 0V, V _{DS} = -15V, f = 1MHz	-	2754	-	pF
C _{oss}	Output Capacitance		-	505	-	pF
C _{rss}	Reverse Transfer Capacitance		-	415	-	pF
Q _g	Total Gate Charge	V _{GS} = 0 to -10V V _{DS} = -15V, I _D = -5A	-	69	-	nC
Q _{gs}	Gate Source Charge		-	12	-	nC
Q _{gd}	Gate Drain("Miller") Charge		-	13	-	nC
Switching Characteristics						
t _{d(on)}	Turn-On DelayTime	V _{GS} = -10V, V _{DD} = -15V I _D = -10A, R _{GEN} = 3Ω	-	12	-	ns
t _r	Turn-On Rise Time		-	72	-	ns
t _{d(off)}	Turn-Off DelayTime		-	78	-	ns
t _f	Turn-Off Fall Time		-	60	-	ns
Drain-Source Diode Characteristics and Max Ratings						
I _S	Maximum Continuous Drain to Source Diode Forward Current	V _{GS} = 0V, I _S = -20A	-	-	-80	A
I _{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	-320	A
V _{SD}	Drain to Source Diode Forward Voltage		-	-	-1.2	V
trr	Body Diode Reverse Recovery Time		-	23	-	ns
Qrr	Body Diode Reverse Recovery Charge		I _F = -20A, di/dt = 100A/us	-	50	-

Notes:

1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature.
2. E_{AS} condition: Starting $T_J = 25^\circ\text{C}$, $V_{DD} = -15\text{V}$, $V_G = 10\text{V}$, $R_G = 25\Omega$, $L = 0.5\text{mH}$, $I_{AS} = -42\text{A}$
3. Pulse Test: Pulse Width $\leq 300\mu\text{s}$, Duty Cycle $\leq 0.5\%$.

Test Circuit

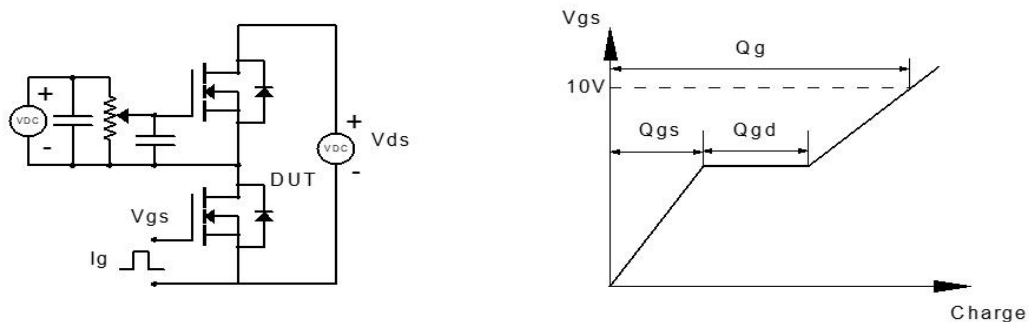


Figure 1: Gate Charge Test Circuit & Waveform

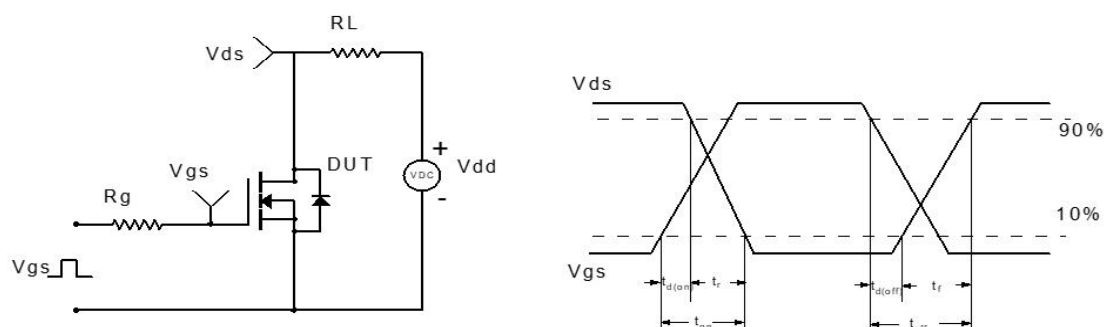


Figure 2: Resistive Switching Test Circuit & Waveform

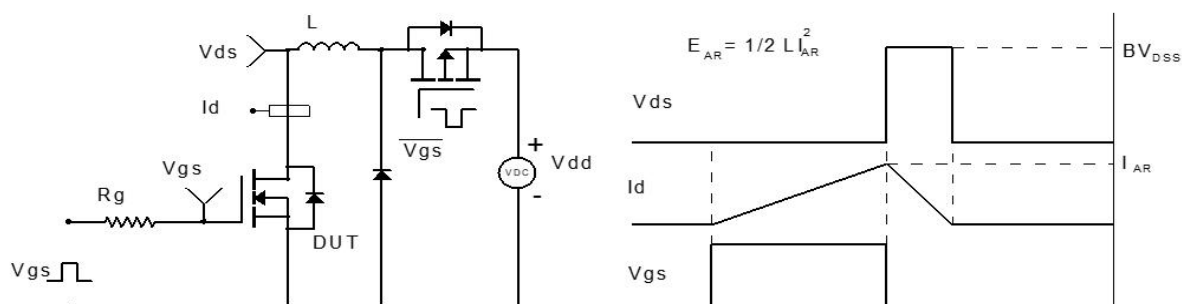


Figure 3: Unclamped Inductive Switching Test Circuit & Waveform

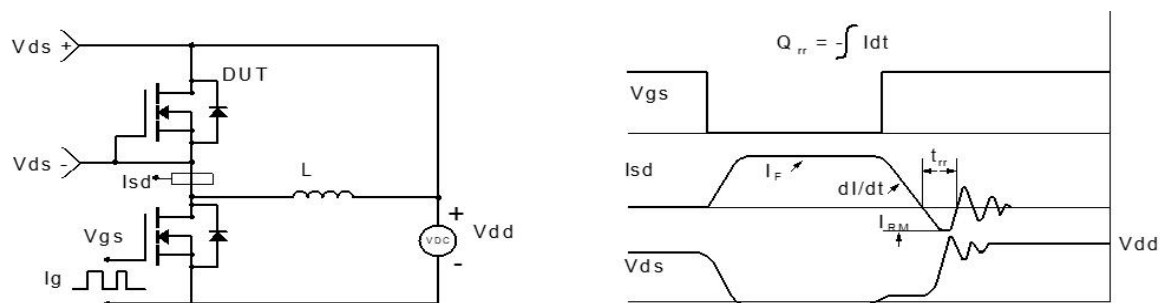
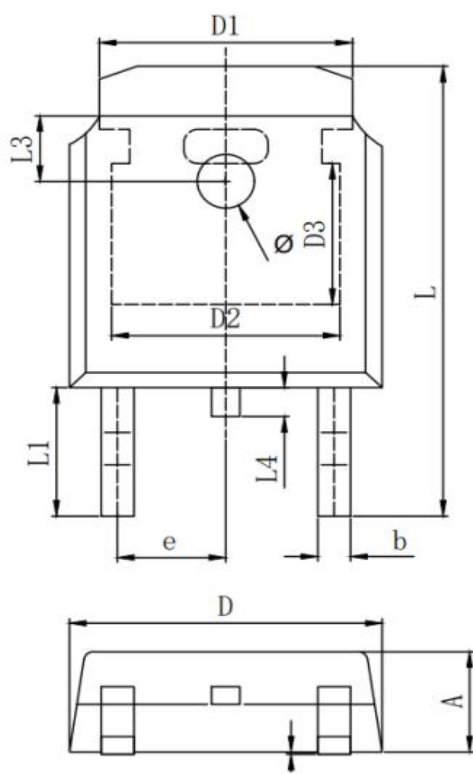


Figure 4: Diode Recovery Test Circuit & Waveform

Package Mechanical Data(TO-252-3L)



SYMBOL	MILLIMETER		
	MIN	Typ.	MAX
A	2.200	2.300	2.400
A1	0.000		0.127
b	0.640	0.690	0.740
c (电镀后)	0.460	0.520	0.580
D	6.500	6.600	6.700
D1	5.334 REF		
D2	4.826 REF		
D3	3.166 REF		
E	6.000	6.100	6.200
e	2.286 TYP		
h	0.000	0.100	0.200
L	9.900	10.100	10.300
L1	2.888 REF		
L2	1.400	1.550	1.700
L3	1.600 REF		
L4	0.600	0.800	1.000
Φ	1.100	1.200	1.300
θ	0°		8°
θ_1	9° TYP		
θ_2	9° TYP		